

PNP germanium transistor for high voltage neon driver, solenoid and relay driver circuits.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	v _{cb}	50	Vdc
Collector-Emitter Voltage	V _{CES}	50	Vdc
Emitter-Base Voltage	V _{EB}	10	Vdc
Collector Current	I _C	200	mA
Collector Dissipation at $T_A = 25^{\circ}C$	P _D	150	mW
derating factor		2.0	mW/°C
Junction Temperature Range	т _Ј	-65 to +100	°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector-Base Cutoff Current ($V_{CB} = 5 Vdc, I_E = 0$)	^I сво		7.0	μAdc
Emitter-Base Cutoff Current ($V_{EB} = 5 Vdc, I_C = 0$)	I _{EBO}		7.0	μAdc
Collector-Emitter Leakage Current (V _{CB} = 50 Vdc, R _{BE} = 0)	ICES		150	μAdc
Collector-Base Breakdown Voltage ($I_C = 25 \ \mu Adc$, $I_E = 0$)	^{вv} сво	50		Vdc
Emitter-Base Breakdown Voltage ($I_E = 25 \ \mu Adc, I_C = 0$)	^{BV} EBO	10		Vdc
Collector-Emitter Punch-Thru Voltage ($I_E = 25 \ \mu Adc$)	v _{pt}	50		Vdc
Base-Emitter Input Voltage (I _B = 1.0 mAdc, V _{CE} = 1.0 Vdc)	v _{BE}		0.6	Vdc
DC Current Gain ($V_{CE} = 1 Vdc, I_B = 1 mAdc$)	h _{FE}	10		
Small Signal Current Gain (V _{CE} = 5.0 Vdc, I _E = 1.0 mA, f = 1 kHz)	h _{fe}	10		
Output Admittance (V _{CB} = 5.0 Vdc, I _E = 1.0 mA, f = 1 kHz)	h _{ob}		2.0	µmhos